

Automotive P-Channel 100 V (D-S) 175 °C MOSFET

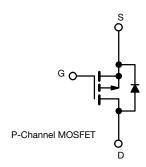
PRODUCT SUMMARY				
V _{DS} (V)	-100			
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = -10 V	0.0190			
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = -4.5 V	0.0222			
I _D (A)	-93			
Configuration	Single			
Package	TO-263			

TO-263

FEATURES

- TrenchFET[®] power MOSFET
- Package with low thermal resistance
- 100 % $R_{\rm q}$ and UIS tested
- AEC-Q101 qualified ^d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \degree C$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	-100	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C	- I _D	-93	
	T _C = 125 °C		-53	
Continuous Source Current (Diode Conduction) ^a		I _S	-120	А
Pulsed Drain Current ^b		I _{DM}	-200	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-70	
Single Pulse Avalanche Energy		E _{AS}	245	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	D	375	w
	T _C = 125 °C	P _D	125	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/W	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

1

SQM100P10-19L



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	-							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$		-100	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$		-2.0	-2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -100 V	-	-	-1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -100 V, T _J = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V_{DS} = -100 V, T _J = 175 °C	-	-	-250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-93	-	-	Α	
		$V_{GS} = -10 \text{ V}$	I _D = -30 A	-	0.0155	0.0190	Ω	
Drain Source On State Desistance a	Р	$V_{GS} = -10 \text{ V}$	I _D = -30 A, T _J = 125 °C	-	-	0.0342		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}$	I _D = -30 A, T _J = 175 °C	-	-	0.0432		
		$V_{GS} = -4.5 V$	I _D = -20 A	-	0.0177	0.0222		
Forward Transconductance b	9fs	V _{DS} = -15 V, I _D = -30 A		-	50	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	10 800	14 100	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	800	1100		
Reverse Transfer Capacitance	C _{rss}			-	650	850		
Total Gate Charge ^c	Qg				220	350		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -50 \text{ V}, I_D = -50 \text{ A}$	I	37	-	nC	
Gate-Drain Charge ^c	Q _{gd}				51	-]	
Gate Resistance	R _g	f = 1 MHz		1	2.2	3.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = -50 \text{ V}, \text{ R}_L = 1 \Omega$ $\text{I}_D \cong -50 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_g = 1 \Omega$		-	20	30		
Rise Time ^c	t _r			-	21	35	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	110	175		
Fall Time ^c	t _f			-	30	50		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	-200	А	
Forward Voltage	V _{SD}	I _F = -70 A, V _{GS} = 0 V		-	-0.885	-1.5	v	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

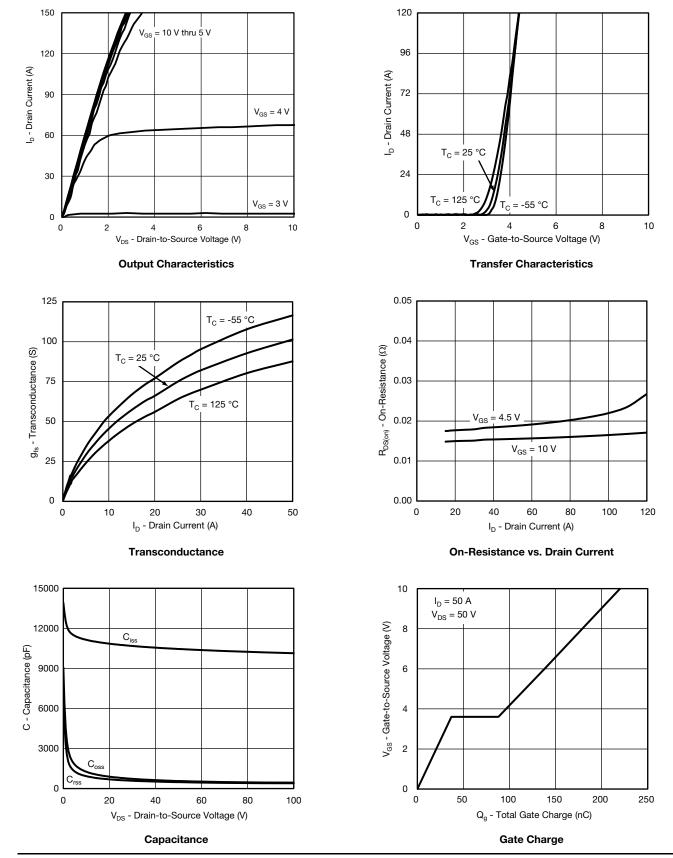
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



S15-2155-Rev. A, 14-Sep-15

3

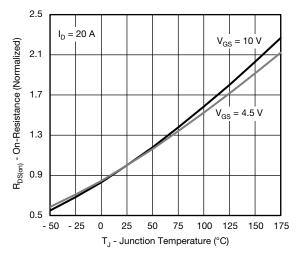
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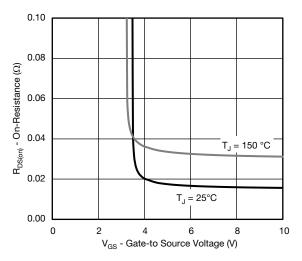
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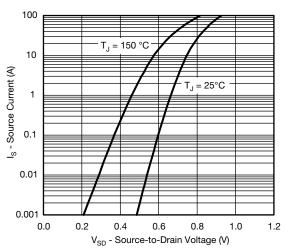
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



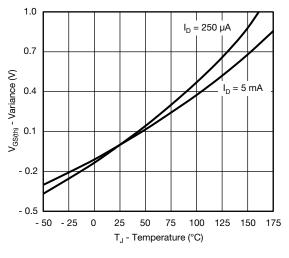
On-Resistance vs. Junction Temperature



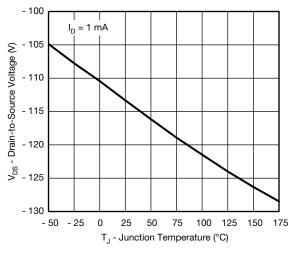
On-Resistance vs. Gate-to-Source Voltage

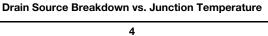


Source Drain Diode Forward Voltage









S15-2155-Rev. A, 14-Sep-15

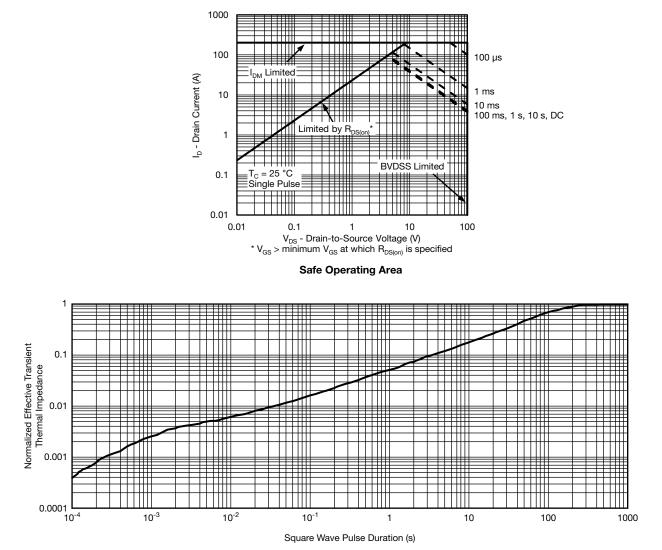
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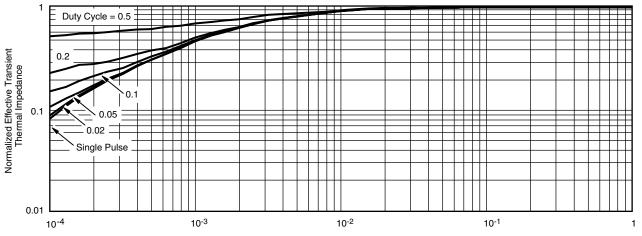
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

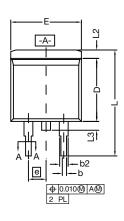
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

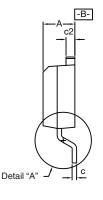
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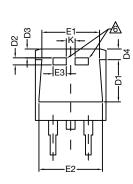


TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

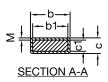








DETAIL A (ROTATED 90°)



		INCHES		MILLIN	IETERS	
DIM.		MIN.	MAX.	MIN.	MAX.	
A		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2 0.038		0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
е		0.100 BSC		2.54 BSC		
К		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	

Notes

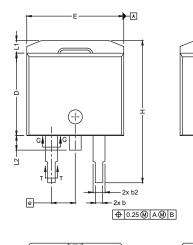
- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
- Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

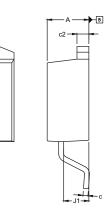
This feature is for thick lead.

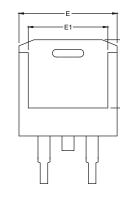
Revison: 28-Oct-2024

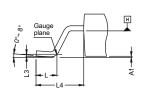


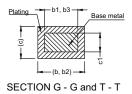
VERSION 2: FACILITY CODE = N











OPTION 1 2 leads



2

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3 leads

DIM.	MIN.	MAX.		
A	4.36	4.56		
A1	0	0.25		
b	0.70	0.90		
b1	0.51	0.89		
b2	1.20	1.46		
b3	1.17	1.37		
с	0.38	0.694		
c1	0.38	0.534		
c2	1.19	1.34		
D	8.60	9.00		
D1	6.9	7.5		
E	10.15	10.55		
E1	8.1	8.7		
e	2.54 BSC			
Н	15.0	15.6		
L	1.9	2.5		
L1	-	1.65		
L2	-	1.78		
L3	0.25 typ.			
L4	4.78	5.28		
J1	2.56	2.96		
ECN: S24-1080-Rev. L, 28-Oct-2024 DWG: 5843				



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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